

N-channel 30 V 6 mΩ logic level MOSFET in LFPAK Rev. 04 — 10 March 2011 Produc

Product data sheet

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- Class-D amplifiers
- DC-to-DC converters

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	30	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	-	-	79	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	55	W
Tj	junction temperature		-55	-	175	°C
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C	-	4.26	6	mΩ
Dynamic o	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$	-	3.08	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
Avalanche	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	-	26	mJ

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering i	nformation		
Type number	Package		
	Name	Description	Version
PSMN6R0-30YL	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

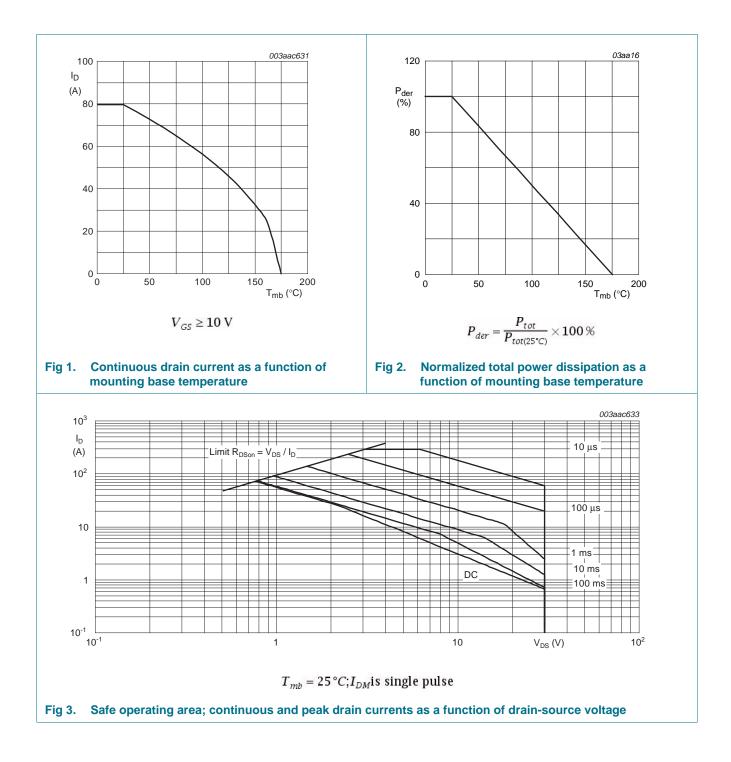
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	30	V
V _{DSM}	peak drain-source voltage	$t_p \le 25 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 110 \text{ nJ};$ pulsed	-	35	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	56	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	79	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	292	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	55	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I _S	source current	T _{mb} = 25 °C	-	73	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	292	А
Avalanche r	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 73 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω ; unclamped	-	26	mJ

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5. Thermal characteristics

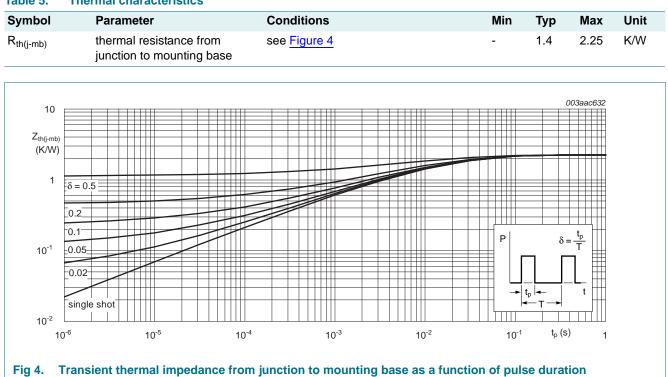


Table 5. Thermal characteristics

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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS} drain-source		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 12	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 12</u>	0.65	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 12</u>	-	-	2.45	V
DSS	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
GSS	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I _D = 15 A; T _j = 25 °C	-	6.18	7.87	mΩ
resis	resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 150 °C; see <u>Figure 13</u>	-	-	10.5	mΩ
		V_{GS} = 10 V; I _D = 15 A; T _j = 25 °C	-	4.26	6	mΩ
R _G	gate resistance	f = 1 MHz	-	0.63	1.5	Ω
Dynamic ch	aracteristics					
Q _{G(tot)} total gate charge	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	24	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	22	-	nC
Q _{GS}	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	4.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.4	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1.8	-	nC
Q _{GD}	gate-drain charge		-	3.08	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.6	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	1425	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	313	-	pF
C _{rss}	reverse transfer capacitance		-	155	-	pF
d(on)	turn-on delay time	V_{DS} = 12 V; R _L = 0.5 Ω; V _{GS} = 4.5 V;	-	25	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	43	-	ns
d(off)	turn-off delay time		-	31	-	ns
t _f	fall time		-	11	-	ns

Symbol

V_{SD}

Source-drain diode

PSMN6R0-30YL

Typ

0.88

Max

1.2

Unit

V

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Min

$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ t_{rr} reverse recovery time 32 -ns $V_{DS} = 20 V$ recovered charge 25 nC Qr --003aac625 003aac627 100 80 10 I_D I_D (A) 4.5 (A) 80 60 60 40 $V_{GS}(V) = 3.2$ 40 3. 20 20 T_i = 150 °C 2.8 25 °C 2.6-24 0 0 2 4 6 8 _{VDS} (V)¹⁰ 0 1 2 3 V_{GS} (V) 4 0 $T_{i} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ $V_{DS} = 10V$ Transfer characteristics: drain current as a Fig 5. Output characteristics: drain current as a Fig 6. function of drain-source voltage; typical values function of gate-source voltage; typical values 003aac630 003aac636 20 2500 С R_{DSor} Cicc (pF) (mΩ) 2000 15 $V_{GS}(V) = 3.2$ Crss 1500 10 4.5 1000 10 5 500 0 0 0 10 20 30 0 2 4 6 8 _{VGS} (V) 10 I_D (A) 40 $T_j = 25 \,^{\circ}C$ $V_{DS} = 0V; f = 1MHz$ Drain-source on-state resistance as a function Fig 8. Input and reverse transfer capacitances as a Fig 7. of drain current; typical values function of gate-source voltage; typical values

Table 6. Characteristics ...continued

Parameter

Tested to JEDEC standards where applicable.

source-drain voltage

Conditions

see Figure 17

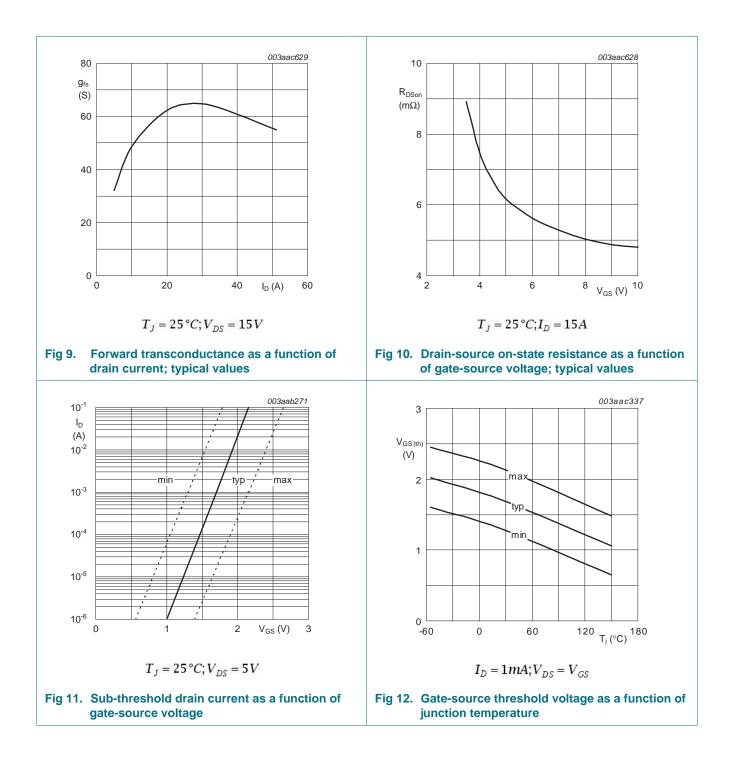
I_S = 25 A; V_{GS} = 0 V; T_i = 25 °C;

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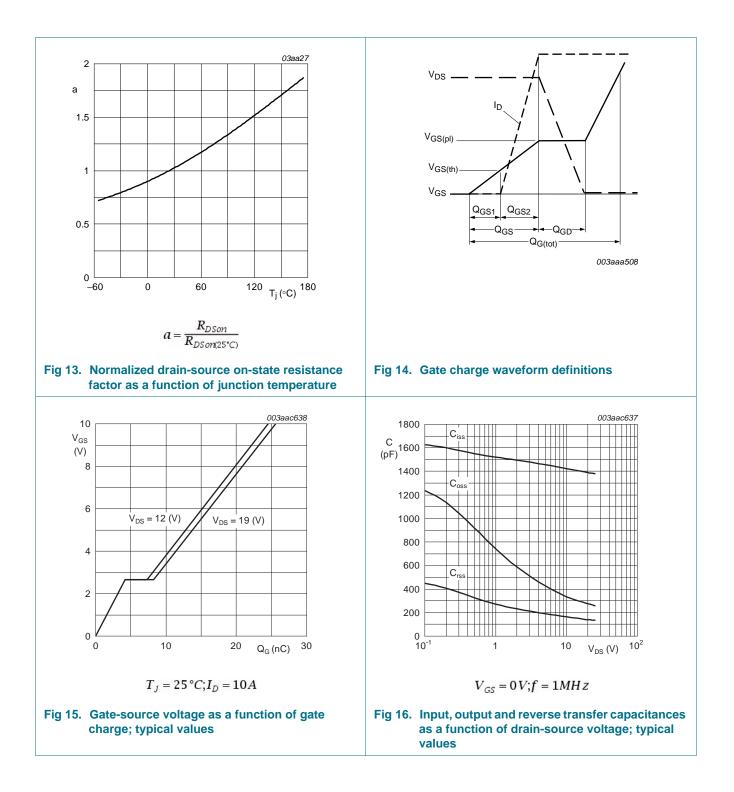
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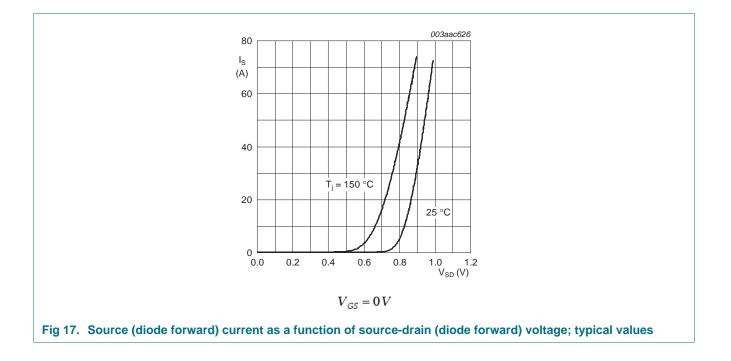
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7. Package outline

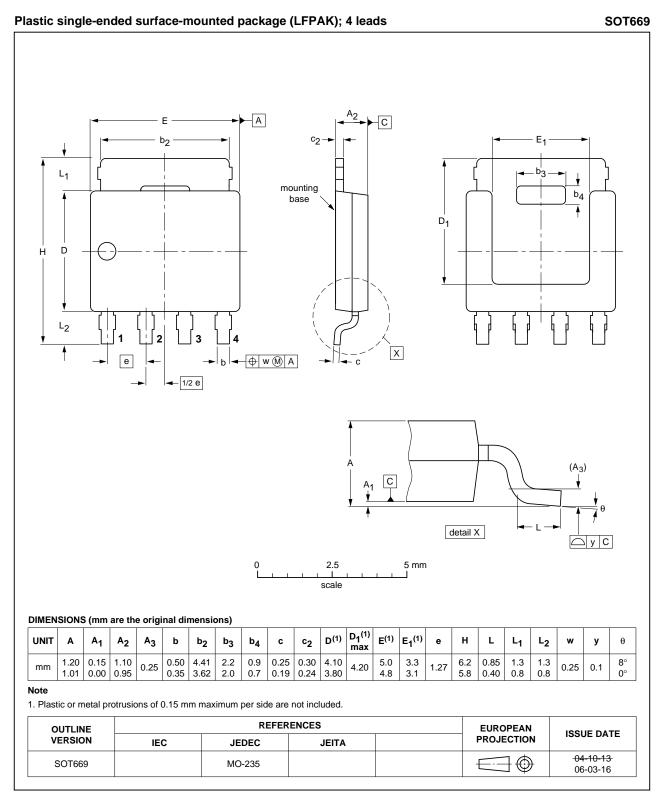


Fig 18. Package outline SOT669 (LFPAK)

PSMN6R0-30YL Product data sheet

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8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R0-30YL v.4	20110310	Product data sheet	-	PSMN6R0-30YL v.3
Modifications:	 Various changes f 	to content.		
PSMN6R0-30YL v.3	20100104	Product data sheet	-	PSMN6R0-30YL v.2

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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